

Kozo Fujiwara

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174
papers

2,734
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27
h-index

43
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180
ext. papers

2,969
ext. citations

3.1
avg, IF

4.74
L-index

#	Paper	IF	Citations
174	Growth of structure-controlled polycrystalline silicon ingots for solar cells by casting. <i>Acta Materialia</i> , 2006 , 54, 3191-3197	8.4	143
173	Directional growth method to obtain high quality polycrystalline silicon from its melt. <i>Journal of Crystal Growth</i> , 2006 , 292, 282-285	1.6	90
172	In situ observation of elementary growth steps on the surface of protein crystals by laser confocal microscopy. <i>Journal of Crystal Growth</i> , 2004 , 262, 536-542	1.6	89
171	Grain growth behaviors of polycrystalline silicon during melt growth processes. <i>Journal of Crystal Growth</i> , 2004 , 266, 441-448	1.6	89
170	Enhanced quantum efficiency of solar cells with self-assembled Ge dots stacked in multilayer structure. <i>Applied Physics Letters</i> , 2003 , 83, 1258-1260	3.4	86
169	Measurement of intrinsic diffusion coefficients of Al and Ni in Ni ₃ Al using Ni/NiAl diffusion couples. <i>Acta Materialia</i> , 2002 , 50, 1571-1579	8.4	85
168	In situ observation of Si faceted dendrite growth from low-degree-of-undercooling melts. <i>Acta Materialia</i> , 2008 , 56, 2663-2668	8.4	74
167	Formation mechanism of parallel twins related to Si-faceted dendrite growth. <i>Scripta Materialia</i> , 2007 , 57, 81-84	5.6	68
166	In situ observations of crystal growth behavior of silicon melt. <i>Journal of Crystal Growth</i> , 2002 , 243, 275-282	2.8	64
165	Growth mechanism of Si-faceted dendrites. <i>Physical Review Letters</i> , 2008 , 101, 055503	7.4	61
164	In-situ observations of melt growth behavior of polycrystalline silicon. <i>Journal of Crystal Growth</i> , 2004 , 262, 124-129	1.6	59
163	Control of compound forming reaction at the interface between SnZn solder and Cu substrate. <i>Journal of Alloys and Compounds</i> , 2005 , 392, 200-205	5.7	47
162	Rational development of new materials--putting the cart before the horse?. <i>Nature Materials</i> , 2004 , 3, 838	27	46
161	Growth of SiGe bulk crystal with uniform composition by directly controlling the growth temperature at the crystal/melt interface using in situ monitoring system. <i>Journal of Crystal Growth</i> , 2001 , 224, 204-211	1.6	46
160	Control of Nucleation Rate for Tetragonal Hen-Egg White Lysozyme Crystals by Application of an Electric Field with Variable Frequencies. <i>Crystal Growth and Design</i> , 2009 , 9, 2420-2424	3.5	44
159	Formation mechanism of a faceted interface: In situ observation of the Si(100) crystal-melt interface during crystal growth. <i>Physical Review B</i> , 2009 , 80,	3.3	43
158	Boron-oxygen defect in Czochralski-silicon co-doped with gallium and boron. <i>Applied Physics Letters</i> , 2012 , 100, 042110	3.4	42

157	Relationship between grain boundary structures in Si multicrystals and generation of dislocations during crystal growth. <i>Journal of Applied Physics</i> , 2010 , 107, 013511	2.5	41
156	Arrangement of dendrite crystals grown along the bottom of Si ingots using the dendritic casting method by controlling thermal conductivity under crucibles. <i>Journal of Crystal Growth</i> , 2011 , 319, 13-18	1.6	41
155	Morphological transformation of a crystal/melt interface during unidirectional growth of silicon. <i>Acta Materialia</i> , 2011 , 59, 4700-4708	8.4	38
154	Floating cast method to realize high-quality Si bulk multicrystals for solar cells. <i>Journal of Crystal Growth</i> , 2009 , 311, 228-231	1.6	34
153	Microstructures of Si multicrystals and their impact on minority carrier diffusion length. <i>Acta Materialia</i> , 2009 , 57, 3268-3276	8.4	34
152	Compositional variation in Si-rich SiGe single crystals grown by multi-component zone melting method using Si seed and source crystals. <i>Journal of Crystal Growth</i> , 2002 , 240, 373-381	1.6	32
151	Role of the Electric Double Layer in Controlling the Nucleation Rate for Tetragonal Hen Egg White Lysozyme Crystals by Application of an External Electric Field. <i>Crystal Growth and Design</i> , 2010 , 10, 2591-2595	3.5	29
150	Ge composition dependence of properties of solar cells based on multicrystalline SiGe with microscopic compositional distribution. <i>Journal of Applied Physics</i> , 2004 , 96, 1238-1241	2.5	28
149	The effect of grain boundary characteristics on the morphology of the crystal/melt interface of multicrystalline silicon. <i>Scripta Materialia</i> , 2013 , 69, 266-269	5.6	27
148	Growth of SiGe bulk crystals with uniform composition by utilizing feedback control system of the crystal/melt interface position for precise control of the growth temperature. <i>Journal of Crystal Growth</i> , 2003 , 250, 298-304	1.6	27
147	Growth of multicrystalline Si with controlled grain boundary configuration by the floating zone technique. <i>Journal of Crystal Growth</i> , 2005 , 280, 419-424	1.6	26
146	Quantitative analysis of subgrain boundaries in Si multicrystals and their impact on electrical properties and solar cell performance. <i>Journal of Applied Physics</i> , 2009 , 105, 044909	2.5	24
145	Crystal Growth Behaviors of Silicon during Melt Growth Processes. <i>International Journal of Photoenergy</i> , 2012 , 2012, 1-16	2.1	23
144	Crystal quality of a 6H-SiC layer grown over macrodefects by liquid-phase epitaxy: a Raman spectroscopic study. <i>Thin Solid Films</i> , 2005 , 476, 206-209	2.2	23
143	Growth mechanism of the Si <110> faceted dendrite. <i>Physical Review B</i> , 2010 , 81,	3.3	22
142	Improvement of crystal quality for tetragonal hen egg white lysozyme crystals under application of an external alternating current electric field. <i>Journal of Applied Crystallography</i> , 2013 , 46, 25-29	3.8	21
141	Formation mechanism of cellular structures during unidirectional growth of binary semiconductor Si-rich SiGe materials. <i>Applied Physics Letters</i> , 2012 , 100, 021903	3.4	21
140	Formation mechanism of twin boundaries during crystal growth of silicon. <i>Scripta Materialia</i> , 2011 , 65, 556-559	5.6	21

139	Control of effect on the nucleation rate for hen egg white lysozyme crystals under application of an external ac electric field. <i>Langmuir</i> , 2011 , 27, 8333-8	4	21
138	Epitaxial relation and island growth of perylene-3,4,9,10-tetracarboxylic dianhydride (PTCDA) thin film crystals on a hydrogen-terminated Si(1 1 1) substrate. <i>Journal of Crystal Growth</i> , 2004 , 262, 196-201	1.6	20
137	In situ observation of twin boundary formation at grain-boundary groove during directional solidification of Si. <i>Scripta Materialia</i> , 2017 , 133, 65-69	5.6	19
136	Nucleation rate enhancement of porcine insulin by application of an external AC electric field. <i>Journal of Crystal Growth</i> , 2012 , 352, 155-157	1.6	19
135	On the origin of strain fluctuation in strained-Si grown on SiGe-on-insulator and SiGe virtual substrates. <i>Applied Physics Letters</i> , 2004 , 85, 1335-1337	3.4	19
134	Effects of high pressure on the growth kinetics of orthorhombic lysozyme crystals. <i>Journal of Crystal Growth</i> , 2003 , 254, 188-195	1.6	19
133	Crystallization of high-quality protein crystals using an external electric field. <i>Journal of Applied Crystallography</i> , 2015 , 48, 1507-1513	3.8	18
132	Impurity partitioning during colloidal crystallization. <i>Journal of Physical Chemistry B</i> , 2013 , 117, 5289-95	3.4	18
131	Generation mechanism of dislocations and their clusters in multicrystalline silicon during two-dimensional growth. <i>Journal of Applied Physics</i> , 2011 , 110, 083530	2.5	18
130	Implementation of faceted dendrite growth on floating cast method to realize high-quality multicrystalline Si ingot for solar cells. <i>Journal of Applied Physics</i> , 2011 , 109, 083527	2.5	18
129	Dependence of Si faceted dendrite growth velocity on undercooling. <i>Applied Physics Letters</i> , 2011 , 98, 012113	3.4	18
128	Influence of the elastic strain on the band structure of ellipsoidal SiGe coherently embedded in the Si matrix. <i>Journal of Applied Physics</i> , 2003 , 94, 916-920	2.5	18
127	Effect of twin spacing on the growth velocity of Si faceted dendrites. <i>Applied Physics Letters</i> , 2010 , 97, 172104	3.4	17
126	Modification of Local Structure and Its Influence on Electrical Activity of Near (310) Σ5 Grain Boundary in Bulk Silicon. <i>Materials Transactions</i> , 2007 , 48, 143-147	1.3	17
125	Effects of spacer thickness on quantum efficiency of the solar cells with embedded Ge islands in the intrinsic layer. <i>Applied Physics Letters</i> , 2004 , 84, 2802-2804	3.4	17
124	Influence of structural imperfection of Σ grain boundaries in bulk multicrystalline Si on their electrical activities. <i>Journal of Applied Physics</i> , 2007 , 101, 063509	2.5	16
123	Physical model for the evaluation of solid-liquid interfacial tension in silicon. <i>Journal of Applied Physics</i> , 2001 , 90, 750-755	2.5	16
122	Impact of local atomic stress on oxygen segregation at tilt boundaries in silicon. <i>Applied Physics Letters</i> , 2017 , 110, 062105	3.4	15

121	Melt growth of multicrystalline SiGe with large compositional distribution for new solar cell applications. <i>Solar Energy Materials and Solar Cells</i> , 2002 , 72, 93-100	6.4	15
120	Growth and properties of SiGe multicrystals with microscopic compositional distribution for high-efficiency solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2002 , 73, 305-320	6.4	15
119	A simple approach to determine preferential growth orientation using multiple seed crystals with random orientations and its utilization for seed optimization to restrain polycrystallization of SiGe bulk crystal. <i>Journal of Crystal Growth</i> , 2005 , 276, 393-400	1.6	15
118	Effects of B and Ge codoping on minority carrier lifetime in Ga-doped Czochralski-silicon. <i>Journal of Applied Physics</i> , 2009 , 106, 013721	2.5	14
117	Structural Origin of a Cluster of Bright Spots in Reverse Bias Electroluminescence Image of Solar Cells Based on Si Multicrystals. <i>Applied Physics Express</i> , 2008 , 1, 075001	2.4	14
116	Effect of the compositional distribution on the photovoltaic power conversion of SiGe solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2007 , 91, 123-128	6.4	14
115	Wave-shaped Si crystal wafers obtained by plastic deformation and preparation of their solar cells. <i>Applied Physics Letters</i> , 2004 , 85, 5896-5898	3.4	14
114	Three-dimensional evaluation of gettering ability for oxygen atoms at small-angle tilt boundaries in Czochralski-grown silicon crystals. <i>Applied Physics Letters</i> , 2015 , 106, 251603	3.4	13
113	Pattern formation mechanism of a periodically faceted interface during crystallization of Si. <i>Journal of Crystal Growth</i> , 2010 , 312, 3670-3674	1.6	13
112	New method for measurement of interdiffusion coefficient in high temperature solutions based on Fick's first law. <i>Journal of Crystal Growth</i> , 2002 , 241, 387-394	1.6	13
111	Structural properties of directionally grown polycrystalline SiGe for solar cells. <i>Journal of Crystal Growth</i> , 2005 , 275, 467-473	1.6	13
110	Effect of grain boundary grooves at the crystal/melt interface on impurity accumulation during the unidirectional growth of multicrystalline silicon. <i>Scripta Materialia</i> , 2016 , 117, 73-76	5.6	12
109	Crystal growth and equilibrium crystal shapes of silicon in the melt. <i>Progress in Photovoltaics: Research and Applications</i> , 2014 , 22, 574-580	6.8	12
108	Realization of Bulk Multicrystalline Silicon with Controlled Grain Boundaries by Utilizing Spontaneous Modification of Grain Boundary Configuration. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 1734-1737	1.4	12
107	Modification of local structures in multicrystals revealed by spatially resolved x-ray rocking curve analysis. <i>Journal of Applied Physics</i> , 2007 , 102, 103504	2.5	12
106	Phase diagram of growth mode for the SiGe/Si heterostructure system with misfit dislocations. <i>Journal of Crystal Growth</i> , 2004 , 260, 372-383	1.6	12
105	In-situ monitoring system of the position and temperature at the crystal/melt interface. <i>Journal of Crystal Growth</i> , 2002 , 236, 125-131	1.6	12
104	In situ observation of interaction between grain boundaries during directional solidification of Si. <i>Scripta Materialia</i> , 2018 , 148, 37-41	5.6	11

103	In situ observation of grain-boundary development from a facet-facet groove during solidification of silicon. <i>Acta Materialia</i> , 2018 , 153, 186-192	8.4	11
102	Liquinert quartz crucible for the growth of multicrystalline Si ingots. <i>Energy Science and Engineering</i> , 2015 , 3, 419-422	3.4	11
101	Instability of crystal/melt interface including twin boundaries of silicon. <i>Applied Physics Letters</i> , 2014 , 104, 182110	3.4	11
100	The critical growth velocity for planar-to-faceted interfaces transformation in SiGe crystals. <i>Applied Physics Letters</i> , 2012 , 100, 141601	3.4	11
99	Effect of various precipitants on the nucleation rate of tetragonal hen egg-white lysozyme crystals in an AC external electric field. <i>Journal of Crystal Growth</i> , 2010 , 312, 3503-3508	1.6	11
98	Impact of Defect Density in Si Bulk Multicrystals on Gettering Effect of Impurities. <i>Japanese Journal of Applied Physics</i> , 2008 , 47, 8790-8792	1.4	11
97	Dependence of Si-Faceted Dendrite Growth Orientation on Twin Spacing and Undercooling. <i>Crystal Growth and Design</i> , 2011 , 11, 1402-1410	3.5	10
96	The impact of Ge codoping on the enhancement of photovoltaic characteristics of B-doped Czochralski grown Si crystal. <i>Journal of Applied Physics</i> , 2012 , 111, 043707	2.5	10
95	Fabrication of SiGe-on-insulator by rapid thermal annealing of Ge on Si-on-insulator substrate. <i>Applied Surface Science</i> , 2004 , 224, 95-98	6.7	10
94	Stacked Ge islands for photovoltaic applications. <i>Science and Technology of Advanced Materials</i> , 2003 , 4, 367-370	7.1	10
93	Growth velocity and grain size of multicrystalline solar cell silicon. <i>Journal of Crystal Growth</i> , 2012 , 356, 17-21	1.6	9
92	Crystal and faceted dendrite growth of silicon near (1 0 0). <i>Acta Materialia</i> , 2012 , 60, 3259-3267	8.4	9
91	High minority carrier lifetime in Ga-doped Czochralski-grown silicon by Ge codoping. <i>Applied Physics Letters</i> , 2009 , 94, 072102	3.4	9
90	Effect of silicon/crucible interfacial energy on orientation of multicrystalline silicon ingot in unidirectional growth. <i>Journal of Applied Physics</i> , 2012 , 112, 113521	2.5	9
89	Molten metal flux growth and properties of CrSi ₂ . <i>Journal of Alloys and Compounds</i> , 2004 , 383, 319-321	5.7	9
88	Effects of vicinal steps on the island growth and orientation of epitaxially grown perylene-3,4,9,10-tetracarboxylic dianhydride (PTCDA) thin film crystals on a hydrogen-terminated Si(1 1 1) substrate. <i>Journal of Crystal Growth</i> , 2005 , 273, 594-602	1.6	9
87	Technique for High-Quality Protein Crystal Growth by Control of Subgrain Formation under an External Electric Field. <i>Crystals</i> , 2016 , 6, 95	2.3	9
86	Effect of an External Electric Field on the Kinetics of Dislocation-Free Growth of Tetragonal Hen Egg White Lysozyme Crystals. <i>Crystals</i> , 2017 , 7, 170	2.3	8

85	Wave-dispersive x-ray spectrometer for simultaneous acquisition of several characteristic lines based on strongly and accurately shaped Ge crystal. <i>Review of Scientific Instruments</i> , 2008 , 79, 033110	1.7	8
84	Fabrication of SiGe-on-Insulator through Thermal Diffusion of Ge on Si-on-Insulator Substrate. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, L232-L234	1.4	8
83	Evidence of the Presence of Built-in Strain in Multicrystalline SiGe with Large Compositional Distribution. <i>Japanese Journal of Applied Physics</i> , 2002 , 41, 4462-4465	1.4	8
82	Grain Boundary Segregation of Impurities During Polycrystalline Colloidal Crystallization. <i>Crystal Growth and Design</i> , 2015 , 15, 5685-5692	3.5	7
81	Growth of congruent-melting lithium tantalate crystal with stoichiometric structure by MgO doping. <i>Journal of Crystal Growth</i> , 2013 , 383, 63-66	1.6	7
80	Growth behavior of faceted Si crystals at grain boundary formation. <i>Journal of Crystal Growth</i> , 2009 , 312, 19-23	1.6	7
79	Point-focusing monochromator crystal realized by hot plastic deformation of a Ge wafer. <i>Journal of Applied Crystallography</i> , 2008 , 41, 798-799	3.8	7
78	Si wafers having one- and two-dimensionally curved (111) planes examined by X-ray diffraction. <i>Journal of Applied Crystallography</i> , 2006 , 39, 443-445	3.8	7
77	Control of Macroscopic Absorption Coefficient of Multicrystalline SiGe by Microscopic Compositional Distribution. <i>Japanese Journal of Applied Physics</i> , 2002 , 41, L37-L39	1.4	7
76	Partitioning of ionic species during growth of impurity-doped lithium niobate by electric current injection. <i>Journal of Crystal Growth</i> , 2014 , 406, 78-84	1.6	6
75	Fabrication of solar cell with stacked Ge islands for enhanced absorption in the infrared regime. <i>Thin Solid Films</i> , 2004 , 451-452, 604-607	2.2	6
74	Effects of growth temperature on the surface morphology of silicon thin films on (111) silicon monocrystalline substrate by liquid phase epitaxy. <i>Journal of Crystal Growth</i> , 2004 , 266, 467-474	1.6	6
73	In situ observation of the Marangoni convection in a NaCl aqueous solutions under microgravity. <i>Journal of Crystal Growth</i> , 2002 , 234, 516-522	1.6	6
72	Simultaneous in situ measurement of solute and temperature distributions in the alloy solutions. <i>Journal of Crystal Growth</i> , 2002 , 242, 313-320	1.6	6
71	High-Quality Crystalline Silicon Layer Grown by Liquid Phase Epitaxy Method at Low Growth Temperature. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, L217-L219	1.4	6
70	Growth and properties of SiGe multicrystals with microscopic compositional distribution and their applications for high-efficiency solar cells. <i>Journal of Crystal Growth</i> , 2005 , 275, e455-e460	1.6	6
69	Hemisphere-shaped silicon crystal wafers obtained by plastic deformation and preparation of their solar cells. <i>Journal of Electronic Materials</i> , 2005 , 34, 1047-1052	1.9	6
68	In situ observation of grain boundary groove at the crystal/melt interface in Cu. <i>Scripta Materialia</i> , 2018 , 146, 169-172	5.6	6

67	Crystallization and re-melting of Si _{1-x} Ge _x alloy semiconductor during rapid cooling. <i>Journal of Alloys and Compounds</i> , 2019 , 798, 493-499	5.7	5
66	The in situ observation of faceted dendrite growth during the directional solidification of GaSb. <i>Scripta Materialia</i> , 2019 , 168, 56-60	5.6	5
65	A {112} grain boundary generated from the decomposition of a grain boundary in multicrystalline silicon during directional solidification. <i>Scripta Materialia</i> , 2019 , 167, 46-50	5.6	5
64	Investigation of defect structure of impurity-doped lithium niobate by combining thermodynamic constraints with lattice constant variations. <i>Journal of Applied Physics</i> , 2015 , 117, 014102	2.5	5
63	The effect of grain boundaries on instability at the crystal/melt interface during the unidirectional growth of Si. <i>Materialia</i> , 2019 , 7, 100386	3.2	5
62	Control of Gibbs free energy relationship between hen egg white lysozyme polymorphs under application of an external alternating current electric field. <i>Journal of Applied Crystallography</i> , 2012 , 45, 207-212	3.8	5
61	Systematic studies of Si and Ge hemispherical concave wafers prepared by plastic deformation. <i>Journal of Crystal Growth</i> , 2009 , 311, 4587-4592	1.6	5
60	Ga segregation during Czochralski-Si crystal growth with Ge codoping. <i>Journal of Crystal Growth</i> , 2010 , 312, 2865-2870	1.6	5
59	Interfacial observations of Ni/Ni ₃ Si and Ni/Ni ₃ Ga diffusion couples. <i>Philosophical Magazine Letters</i> , 1997 , 75, 149-154	1	5
58	Improvement in the conversion efficiency of single-junction SiGe solar cells by intentional introduction of the compositional distribution. <i>Journal of Applied Physics</i> , 2007 , 101, 054504	2.5	5
57	Growth of InGaAs and SiGe homogeneous bulk crystals which have complete miscibility in the phase diagrams. <i>International Journal of Materials and Product Technology</i> , 2005 , 22, 185	1	5
56	Solar cell system using a polished concave Si-crystal mirror. <i>Solar Energy Materials and Solar Cells</i> , 2005 , 88, 323-329	6.4	5
55	Floating Zone Growth of Si Bicrystals Using Seed Crystals with Artificially Designed Grain Boundary Configuration. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, L778-L780	1.4	5
54	On the Origin of Improved Conversion Efficiency of Solar Cells Based on SiGe with Compositional Distribution. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 857-860	1.4	5
53	Liquid Phase Epitaxial Growth of Si Layers on Si Thin Substrates from Si Pure Melts under Near-Equilibrium Conditions. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 5092-5095	1.4	5
52	Liquid immiscibility in a CTGS (Ca ₃ TaGa ₃ Si ₂ O ₁₄) melt. <i>Journal of Crystal Growth</i> , 2016 , 454, 82-86	1.6	5
51	Crystal Growth Conditions of Types I and II NaBi Clathrates by Evaporation of Na from a NaBi Solution. <i>Crystal Growth and Design</i> , 2018 , 18, 351-355	3.5	5
50	In-situ observation of instability of a crystal/melt interface during the directional growth of pure antimony. <i>AIP Advances</i> , 2018 , 8, 075121	1.5	5

49	Application of weighted Voronoi diagrams to analyze nucleation sites of multicrystalline silicon ingots. <i>Journal of Crystal Growth</i> , 2018 , 499, 62-66	1.6	4
48	Effect of misorientation angle of grain boundary on the interaction with Σ boundary at crystal/melt interface of multicrystalline silicon. <i>Materialia</i> , 2019 , 7, 100357	3.2	4
47	Plastically deformed Si-crystal wafers for neutron-monochromator elements. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2011 , 635, 137-140	1.2	4
46	Realization of a High-Performance Point-Focusing Monochromator for X-ray Studies. <i>Applied Physics Express</i> , 2010 , 3, 046601	2.4	4
45	Suppression of structural imperfection in strained Si by utilizing SiGe bulk substrate. <i>Applied Physics Letters</i> , 2006 , 88, 221912	3.4	4
44	Fabrication of SiGe bulk crystals with uniform composition as substrates for Si-based heterostructures. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002 , 89, 364-367	3.1	4
43	Effect of Solid-Liquid Interface Morphology on Grain Boundary Segregation during Colloidal Polycrystallization. <i>Crystal Growth and Design</i> , 2016 , 16, 2765-2770	3.5	4
42	Origin of small-angle grain boundaries during directional solidification in multicrystalline silicon. <i>Materialia</i> , 2018 , 3, 347-352	3.2	4
41	Effect of point defects on Curie temperature of lithium niobate. <i>Journal of the American Ceramic Society</i> , 2017 , 100, 1118-1124	3.8	3
40	Grain Growth in the Melt 2015 , 723-748		3
39	Influence of interfacial structure on propagating direction of small-angle grain boundaries during directional solidification of multicrystalline silicon. <i>Scripta Materialia</i> , 2019 , 172, 105-109	5.6	3
38	Grown-in microdefects and photovoltaic characteristics of heavily Ge co-doped Czochralski-grown p-type silicon crystals. <i>Scripta Materialia</i> , 2013 , 69, 686-689	5.6	3
37	Fabrication of Quasi-Phase-Matching Structure during Pseudoepitaxial Borate Crystal Growth. <i>Applied Physics Express</i> , 2013 , 6, 015501	2.4	3
36	High-Efficiency Concave and Conventional Solar Cell Integration System Using Focused Reflected Light. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 1664-1667	1.4	3
35	Intermixing of Ge and Si during exposure of GeH ₄ on Si. <i>Thin Solid Films</i> , 2006 , 508, 163-165	2.2	3
34	Growth of SiGe-on-insulator and its application as a substrate for epitaxy of strained-Si layer. <i>Journal of Crystal Growth</i> , 2005 , 275, e1203-e1207	1.6	3
33	Evaluation of the diffusion coefficients in liquid GaGe binary alloys using a novel method based on Fick's first law. <i>Journal of Non-Crystalline Solids</i> , 2002 , 312-314, 196-202	3.9	3
32	In situ observation of the solidification interface and grain boundary development of two silicon seeds with simultaneous measurement of temperature profile and undercooling. <i>Journal of Crystal Growth</i> , 2020 , 532, 125428	1.6	3

31	The solid-solution region for the langasite-type $\text{Ca}_3\text{TaGa}_3\text{Si}_2\text{O}_{14}$ crystal as determined by a lever rule. <i>Journal of Crystal Growth</i> , 2015 , 415, 111-117	1.6	2
30	Germanium-doped Czochralski silicon: a novel material for solar cells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 1746-1749		2
29	Crystal growth under external electric fields 2014 ,		2
28	Formation mechanism of twin boundaries in lithium tetraborate. <i>Journal of Crystal Growth</i> , 2011 , 331, 78-82	1.6	2
27	Development of high-resolution and light-weight x-ray optics with deformed silicon wafers 2009 ,		2
26	Influence of growth temperature and cooling rate on the growth of Si epitaxial layer by dropping-type liquid phase epitaxy from the pure Si melt. <i>Journal of Crystal Growth</i> , 2008 , 310, 5248-5251 ^{1,6}	1.6	2
25	High-Temperature Solution Growth and Characterization of Chromium Disilicide. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, 7292-7293	1.4	2
24	Analysis of the Dark-Current Density in Solar Cells Based on Multicrystalline SiGe. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 8019-8022	1.4	2
23	Strain distribution of Si thin film grown on multicrystalline-SiGe with microscopic compositional distribution. <i>Journal of Applied Physics</i> , 2002 , 92, 7098-7101	2.5	2
22	In situ observation of multiple parallel (1 1 1) twin boundary formation from step-like grain boundary during Si solidification. <i>Applied Physics Express</i> , 2020 , 13, 105501	2.4	2
21	Fundamental Understanding of Subgrain Boundaries. <i>Advances in Materials Research</i> , 2009 , 83-95		2
20	Effect of twin boundary formation on the growth rate of the GaSb{111} plane. <i>Acta Materialia</i> , 2020 , 185, 453-460	8.4	2
19	Segregation mechanism of arsenic dopants at grain boundaries in silicon. <i>Science and Technology of Advanced Materials Methods</i> , 2021 , 1, 169-180		2
18	In-situ studies of multicrystalline silicon nucleation and growth on Si and Si_3N_4 coated substrates. <i>Journal of Crystal Growth</i> , 2018 , 482, 75-84	1.6	2
17	Segregation of Ge in B and Ge codoped Czochralski-Si crystal growth. <i>Journal of Alloys and Compounds</i> , 2015 , 639, 588-592	5.7	1
16	The impact of Ge codoping on grown-in O precipitates in Ga-doped Czochralski-silicon. <i>Journal of Crystal Growth</i> , 2011 , 321, 24-28	1.6	1
15	One-dimensionally curved Si and Ge single crystal wafers prepared by hot-pressing: potential performance for optical components for X-ray diffraction. <i>Journal of Physics: Conference Series</i> , 2007 , 83, 012030	0.3	1
14	Influence of growth temperature on minority-carrier lifetime of Si layer grown by liquid phase epitaxy using Ga solvent. <i>Journal of Applied Physics</i> , 2005 , 98, 073708	2.5	1

13	Mechanism of Dendrite Crystal Growth. <i>Advances in Materials Research</i> , 2009 , 71-82		1
12	Orientation-dependent impurity partitioning of colloidal crystals. <i>Journal of Crystal Growth</i> , 2016 , 439, 13-18	1.6	1
11	Investigation of Si Dendrites by Electron-Beam-Induced Current. <i>Crystals</i> , 2018 , 8, 317	2.3	1
10	Seeded Growth of Type-II Na ₂₄ Si ₁₃₆ Clathrate Single Crystals. <i>Crystals</i> , 2021 , 11, 808	2.3	1
9	Dynamics at crystal/melt interface during solidification of multicrystalline silicon. <i>High Temperature Materials and Processes</i> , 2022 , 41, 31-47	0.9	0
8	Evaluation of crystalline silicon solar cells by current-modulating four-point-probe method. <i>Applied Physics Letters</i> , 2013 , 103, 043903	3.4	
7	?????????????????. <i>Materia Japan</i> , 2006 , 45, 720-724	0.1	
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4	Twin boundary formation at a grain-boundary groove during the directional solidification of InSb. <i>Journal of Crystal Growth</i> , 2022 , 577, 126403	1.6	
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